Abstracts

A Nonlinear GaAs FET Model for Use in the Design of Output Circuits for Power Amplifiers (Dec. 1985 [T-MTT])

W.R. Curtice and M. Ettenberg. "A Nonlinear GaAs FET Model for Use in the Design of Output Circuits for Power Amplifiers (Dec. 1985 [T-MTT])." 1985 Transactions on Microwave Theory and Techniques 33.12 (Dec. 1985 [T-MTT] (1985 Symposium Issue)): 1383-1394.

A nonlinear equivalent circuit model for the GaAs FET has been developed based upon the small-signal device model and separate current measurements, including drain-gate avalanche current data. The harmonic-balance technique is used to develop the FET RF load-pull characteristics in an amplifier configuration under large-signal operation. Computed and experimental load-pull results show good agreement.

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